

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S414	4	"557746".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/09 10:35
S415	16	((("4058524") or ("6089869") or ("5190850") or ("6074937") or ("8203842"))).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/06/09 10:37
S416	13	("5254484" "5585286" "5953615").PN. OR ("6074937").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/09 10:38
S417	3	"04058524"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:42
S418	3	"06089869"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:43
S419	3	"05190850"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:44
S420	2	"08203842"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:44
S421	23	"5602045"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/09 10:45
S422	1123	solid phase epitaxy	US-PGPUB; USPAT	ADJ	ON	2009/06/20 18:32
S423	725	solid phase epitaxy and @ad<"20040331"	US-PGPUB; USPAT	ADJ	ON	2009/06/20 18:32
S424	858	solid phase epitaxy and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/20 18:32

S425	18	solid phase epitaxy and amorphous and restore and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/20 18:37
S426	182	solid phase epitaxy and amorphous and recrystal \$7 and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/06/20 18:38
S427	38	(US-20040235280-\$ or US-20050003638-\$ or US-20050136623-\$ or US-20050148125-\$ or US-20050093032-\$ or US-20040132260-\$ or US-20040115892-\$ or US-20040115889-\$).did. or (US-6521502-\$ or US-7094671-\$ or US-7247547-\$ or US-7091097-\$ or US-6680250-\$ or US-6555439-\$ or US-6548361-\$ or US-6391751-\$ or US-6074937-\$ or US-6624037-\$ or US-6455385-\$ or US-6387782-\$ or US-6329704-\$ or US-5602045-\$ or US-6982212-\$ or US-6933579-\$ or US-6743680-\$ or US-6689671-\$ or US-6630386-\$ or US-6620671-\$ or US-6534373-\$ or US-6506650-\$ or US-6362063-\$ or US-6008098-\$).did. or (JP-04058524-\$ or JP-06089869-\$ or JP-05190850-\$).did. or (JP-08203842-\$ or US-6521502-\$ or US-6534373-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2009/06/20 20:24
S428	27	(SPE or solid phase epitaxy)and S427	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/20 20:25
S429	28	(SPE or solid phase epitax \$3)and S427	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/20 21:08
S430	24	(SPE or solid phase epitax \$3)and S427	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/20 21:09
S431	25	deep near amorphiz\$5	US-PGPUB; USPAT	OR	ON	2009/06/21 20:44
S432	29	deep near amorphiz\$5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/06/21 20:44

S433	13	deep near amorphiz\$5 and (solid phase epitaxy or SPE or low temperature anneal\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 20:48
S434	7	part\$3 (crystal\$6 or recrystal\$6) same amorphiz\$5 and (solid phase epitaxy or SPE or low temperature anneal\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 21:02
S435	17	part\$3 (crystal\$6 or recrystal\$6) and amorphiz\$5 and (solid phase epitaxy or SPE or low temperature anneal\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 21:05
S436	84	part\$3 (crystal\$6 or recrystal\$6) and (amorphiz\$5 or amorphous or a-Si) and (solid phase epitaxy or SPE or low temperature anneal\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	NEAR	ON	2009/06/21 21:06
S437	1104	low temperature anneal\$3 and amorphous	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 13:56
S438	15	part\$3 with low temperature anneal\$3 and amorphous	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:33
S439	22	low temperature anneal\$3 and part\$3 amorphous	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:35
S440	860	low temperature anneal\$3 and amorphous and (recrystal\$8 or crystal\$7)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:38
S441	569	low temperature anneal\$3 and amorphous and (recrystal\$8 or crystal\$7) and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 15:39
S442	289	low temperature anneal\$3 and amorphous and (recrystal\$8 or crystal\$7) and defects and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 19:06
S443	277	partial near recrystalliz\$5	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 19:41
S444	1608	partial near (recrystalliz\$5 or crystalliz\$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:02
S445	1336	partial near (crystalliz\$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:02

S446	4124	part\$3 near (crystalliz\$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:11
S447	778	part\$3 near (recrystalliz \$5)	US-PGPUB; USPAT; USOCR; FPRS	NEAR	ON	2009/06/29 20:11
S448	8	"465075".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/30 13:18
S449	7	"117125".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/30 13:34
S450	6	"110826".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/06/30 13:42
S451	32	solid state epitaxy	US-PGPUB; USPAT; USOCR; FPRS	ADJ	ON	2009/07/05 23:34
S452	35	solid state epitaxy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:34
S453	2926	low temperature anneal\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:41
S454	257	low temperature anneal\$3 same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:42
S455	185	low temperature anneal\$3 same amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:42
S456	527	low temperature anneal\$3 and amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/05 23:58
S457	2170	(low temperature anneal\$3 or SPE or solid phase epitax \$3) and amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/06 00:24
S458	921	(low temperature anneal\$3 or SPE or solid phase epitax \$3) same amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2009/07/06 00:24

S459	13	amorphous-crystal interface	US-PGPUB; USPAT; USOCR; FPRS	ADJ	ON	2009/07/06 10:24
S460	10	("20010041432" "20020058385" "5171703" "6184112" "6190179" "6333217" "6368928" "6432802" "6696341").PN. OR ("7141477").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/06 10:59
S461	321	amorphous crystal (spe or sper or solid phase epitaxy)	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/06 11:05
S462	2754	amorphous crystal (spe or sper or solid phase epitaxy) and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 11:58
S463	58	amorphous partial near8 crystal (spe or sper or solid phase epitaxy)and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 11:58
S464	91	amorphous partial near8 crystal\$8 (spe or sper or solid phase epitaxy)and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 11:59
S465	47	amorphous partial near8 crystal\$8 (spe or sper or solid phase epitaxy)source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:00
S466	54	partial near8 crystal\$8 (spe or sper or solid phase epitaxy)source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:01
S467	58	partial near8 (re\$crystal\$8 OR crystal\$8) (spe or sper or solid phase epitaxy) source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:01
S468	479	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re\$crystal\$8 OR crystal\$8) (spe or sper or solid phase epitaxy)source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:02
S469	453	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re\$crystal\$8 OR crystal\$8) (spe or sper or solid phase epitaxy)source drain GATE and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:02

S470	65	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re\$crystal\$8 OR crystal\$8) (spe or sper or solid phase epitaxy)source drain GATE (GERMANIUM OR SILICON OR ANTIMONY OR INDIUM) NEAR IONS and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/06 12:03
S471	65	(SUB-LAYER OR SECTION OR partial OR PORTION) near8 (re\$crystal\$8 OR crystal\$8) (spe or sper or solid phase epitaxy)source drain GATE (GERMANIUM OR SILICON OR ANTIMONY OR INDIUM) NEAR IONS and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/06 12:03
S472	145	(spe or sper or solid phase epitaxy)source drain GATE (GERMANIUM OR SILICON OR ANTIMONY OR INDIUM) NEAR IONS and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/06 12:19
S473	70	(heat near treat\$4 or anneal\$3) amorphous and preamorph\$5 source drain and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/06 13:13
S474	10	(portion or partial or partially or part) (crystal\$8 or re-crystal\$8 or recrystal\$3) RTA and SPE	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/07 11:53
S475	10	(portion or partial or partially or part) (crystal\$8 or re-crystal\$8 or recrystal\$3) RTA and SPE	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:54
S476	8	two near step (SPE\$1 or solid phase epitaxy) amorphous crystal\$8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:55
S477	95	two near step (SPE\$1 or solid phase epitaxy or heat adj treatment) amorphous crystal\$8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:56
S478	4	two near step (SPE\$1 or solid phase epitaxy or heat adj treatment) amorphous crystal\$8 activat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:57

S479	83	two near step with (SPE\$1 or solid phase epitaxy or heat adj treatment) amorphous crystal\$8 activat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2009/07/07 11:57
S480	4970	(SPE\$1 or solid phase epitaxy) activat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:59
S481	668	(SPE\$1 or solid phase epitaxy) activat\$3 and gate and source	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:59
S482	195	(SPE\$1 or solid phase epitaxy) activat\$3 and gate and source and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	SAME	ON	2009/07/07 11:59
S483	108	(SPE\$1 or solid phase epitaxy) activat\$3 and gate and source and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/07 12:01
S484	32	(SPE\$1 or solid phase epitaxy) activat\$3 and gate and source and amorphous and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/07 12:01
S485	35	(SPE\$1 or solid phase epitaxy) activat\$3 and gate and source and (amorphous or amorphiz \$5) and @ad<"20040331"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	WITH	ON	2009/07/07 12:02
S486	16	"6,063,682"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/07/07 12:52
S487	10	("20030022461" "20030027381" "20030162336" "20040087121" "20050215024" "20050260809" "5948162" "6063682" "6514829" "6548361"). PN. OR ("7122452").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/07/07 12:59
S488	0	sper first near depth second near depth	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/07 13:00
S489	8	sper first near depth second near depth	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/07 13:01

S490	39	low near temperature near anneal\$3 first near depth second near depth	US-PGPUB; USPAT; USOCR; FPRS	AND	ON	2009/07/07 13:01
S491	474	solid near phase near epitax\$3 surface (crystal\$8 or re-crystal\$8 or recrystal \$8)	US-PGPUB; USPAT; USOCR; FPRS	SAME	ON	2009/07/07 13:11
S492	24	"6548361"	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/07/09 11:29
S493	4	"557746".ap.	US-PGPUB; USPAT; USOCR; FPRS	OR	ON	2009/07/09 12:35

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